

G3S06516B

650V/16A Silicon Carbide Power Schottky Barrier Diode

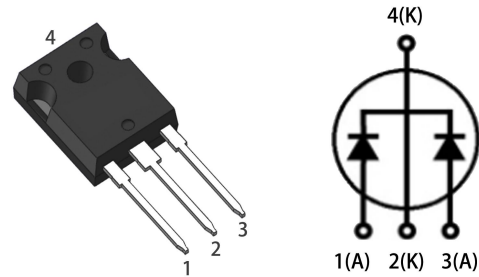
Features

- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- High temperature operation
- High frequency operation

Key Characteristics		
V_{RRM}	650	V
$I_F, T_c \leq 154^\circ\text{C}$	8*	A
Q_C	28*	nC

Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements



Applications

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV



Part No.	Package Type	Marking
G3S06516B	TO-247AB	G3S06516B

*Per leg; **Per device

Maximum Ratings

Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		650	V
Surge Peak Reverse Voltage	V_{RSM}		650	
DC Blocking Voltage	V_{DC}		650	
Continuous Forward Current	I_F	$T_C=25^{\circ}C$ $T_C=125^{\circ}C$ $T_C=154^{\circ}C$	28.4* 14.9* 8*	A
Repetitive Peak Forward Surge Current	I_{FRM}	$T_C=25^{\circ}C$, $t_p=10ms$, Half Sine Wave, $D=0.3$	40*	A
Non-repetitive Peak Forward Surge Current	I_{FSM}	$T_C=25^{\circ}C$, $t_p=10ms$, Half Sine Wave	88*	A
Power Dissipation	P_{TOT}	$T_C=25^{\circ}C$	105*	W
		$T_C=110^{\circ}C$	45*	W
Operating Junction	T_j		-55°C to 175°C	°C
Storage Temperature	T_{stg}		-55°C to 175°C	°C
Mounting Torque		M3 Screw	1	Nm
		6-32 Screw	8.8	lbf-in

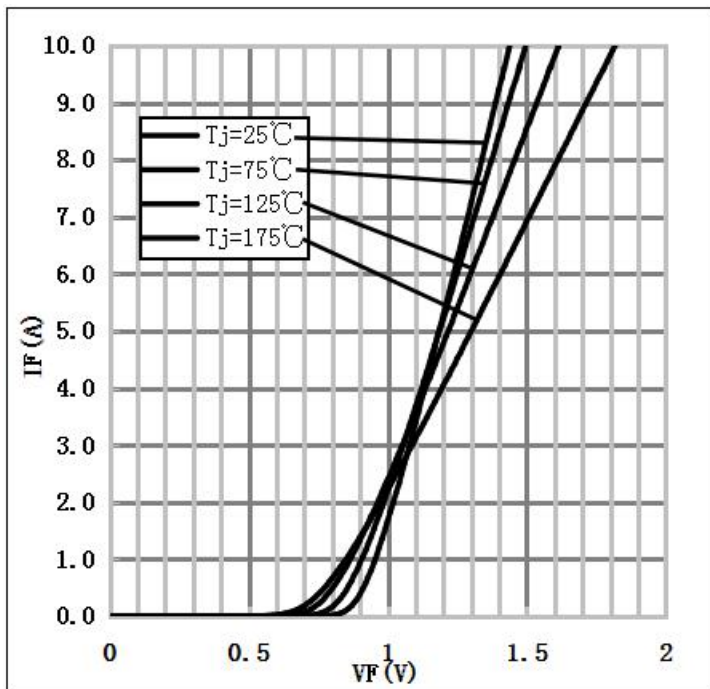
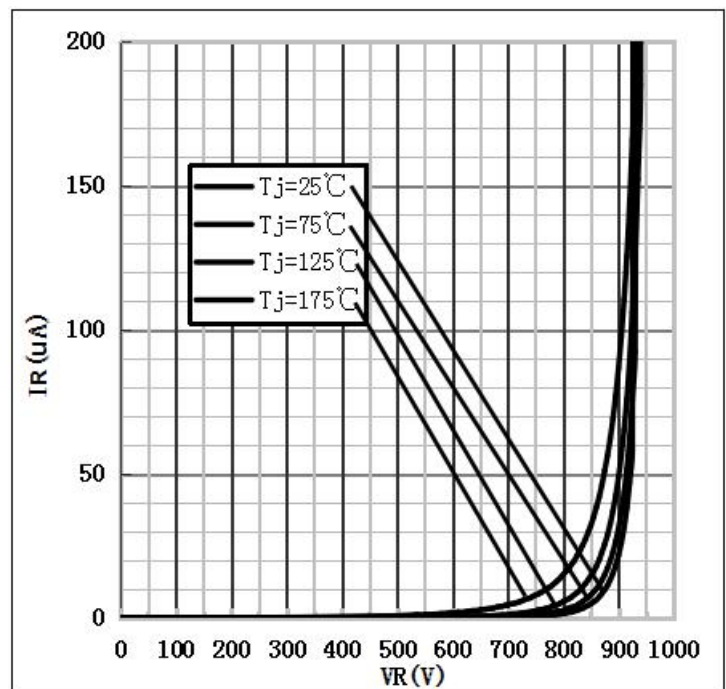
Thermal Characteristics

Parameter	Symbol	Test Condition	Value	Unit
			Typ.	
Thermal resistance from junction to case	R_{thJC}		1.42* 0.71**	°C/W

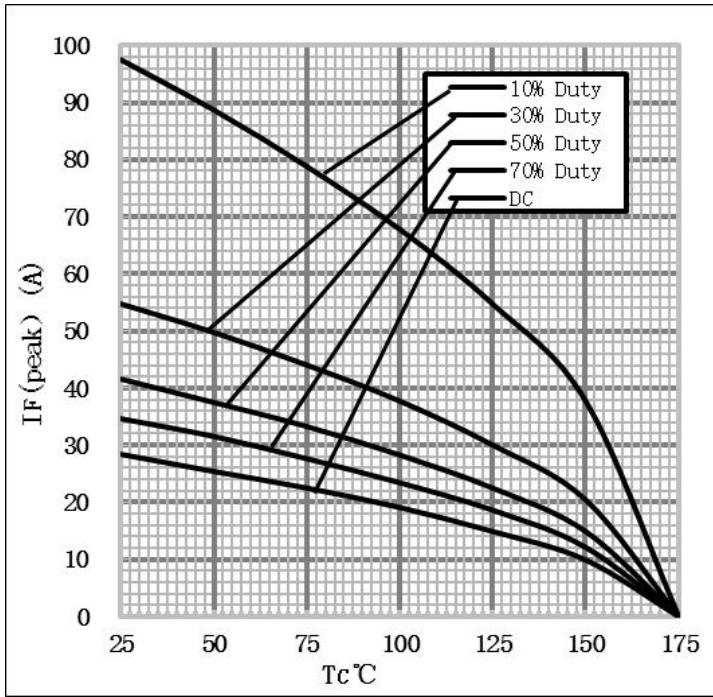
*Per leg; **Per device

Electrical Characteristics(Per leg)

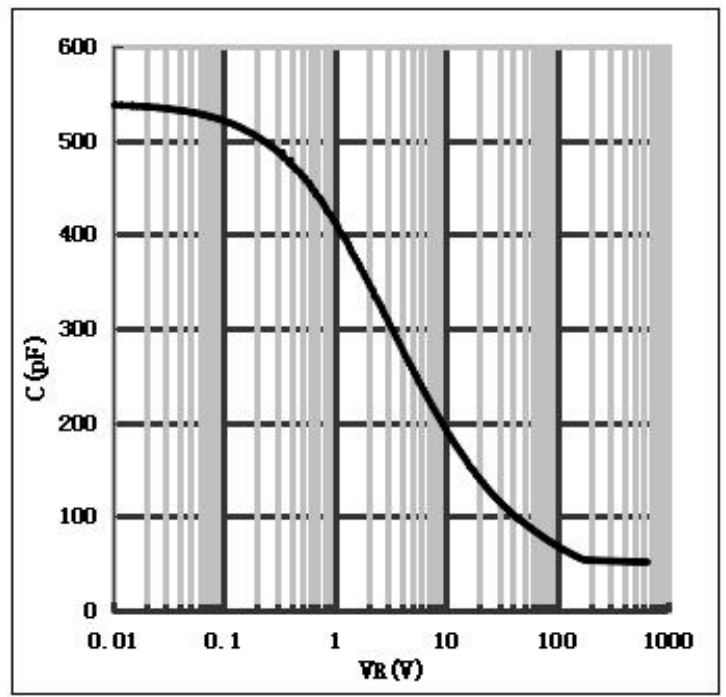
Parameter	Symbol	Test Conditions	Numerical		Unit
			Typ.	Max.	
Forward Voltage	V_F	$I_F=8A, T_j=25^\circ C$	1.35	1.7	V
		$I_F=8A, T_j=175^\circ C$	1.6	2	
Reverse Current	I_R	$V_R=650V, T_j=25^\circ C$	0.55	50	μA
		$V_R=650V, T_j=175^\circ C$	2.5	100	
Total Capacitive Charge	Q_C	$V_R=400V, T_j=150^\circ C$ $Q_C = \int_0^{V_R} C(V)dV$	28	-	nC
Total Capacitance	C	$V_R=0V, T_j=25^\circ C, f=1MHz$	510	-	pF
		$V_R=200V, T_j=25^\circ C, f=1MHz$	53	-	
		$V_R=400V, T_j=25^\circ C, f=1MHz$	52	-	

Performance Graphs(Per leg)1) Forward IV characteristics as a function of T_j :2) Reverse IV characteristics as a function of T_j :

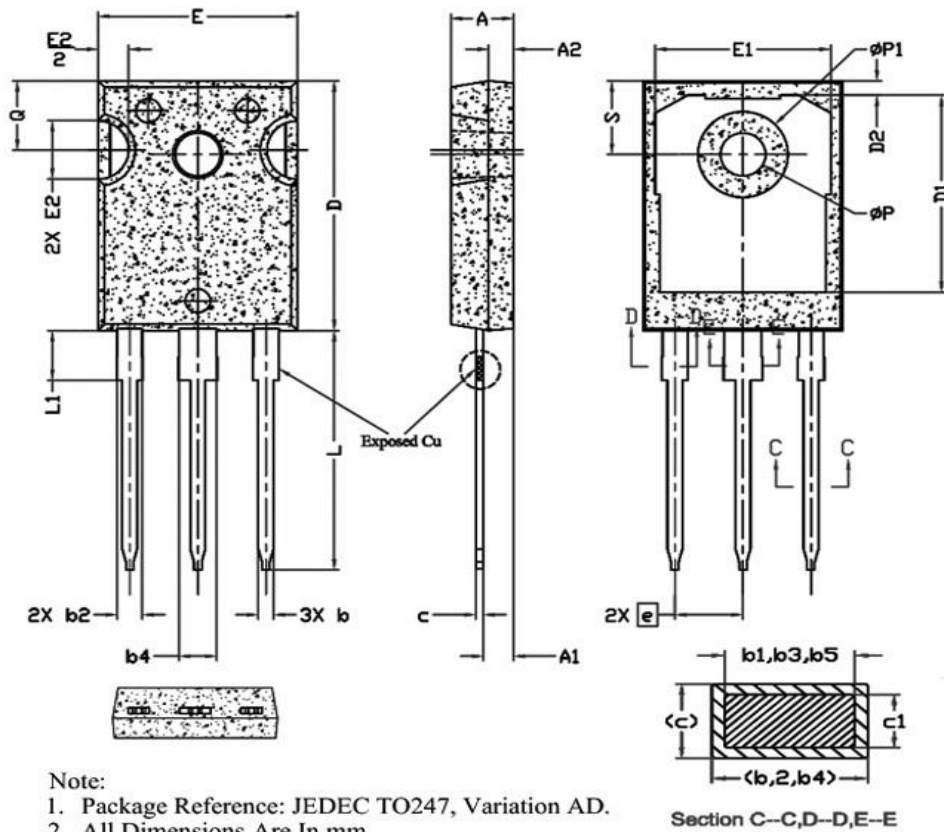
3) Current Derating:



4) Capacitance vs. reverse voltage:



Package TO-247AB



单位: mm

SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.50	2.00	2.49	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.55	0.60	0.69	6
c1	0.55	0.60	0.65	
D	20.80	20.95	21.10	4
D1	16.25	16.55	17.65	5
D2	0.51	1.19	1.35	
E	15.75	15.94	16.13	4
E1	13.46	14.02	14.16	5
E2	4.32	4.91	5.49	3
e	5.44BSC			
L	19.81	20.07	20.32	
L1	4.10	4.19	4.40	6
ØP	3.56	3.61	3.65	7
ØP1	7.19REF.			
Q	5.39	5.79	6.20	
S	6.04	6.17	6.30	

Note:

1. Package Reference: JEDEC TO247, Variation AD.
2. All Dimensions Are In mm.
3. Slot Required, Notch May Be Rounded
4. Dimension D & E Do Not Include Mold Flash. Mold Flash Shall Not Exceed 0.127mm Pre Side. These Dimensions Are Measured At The Outermost Extreme Of The Plastic Body.
5. Thermal Pad Contour Optional Within Dimension D1 & E1.
6. Lead Finish Uncontrolled In L1.
7. ØP To Have A Maximum Draft Angle Of 1.5° To The Top Of The Part With A Maximum Hole Diameter Of 3.91mm.
8. Dimension "b2" And "b4" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.10mm Total In Excess Of "b2" And "b4" Dimension At Maximum Material Condition.

WAFER DIAMETER	WAFER LOT
150 mm	(Up to 13 bit): LT*****、LE*****

Note: The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC(RoHS2).